

DATA SHEET

BFG540; BFG540/X; BFG540/XR NPN 9 GHz wideband transistor

Product specification
File under Discrete Semiconductors, SC14

September 1995

NPN 9 GHz wideband transistor

**BFG540; BFG540/X;
BFG540/XR**

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

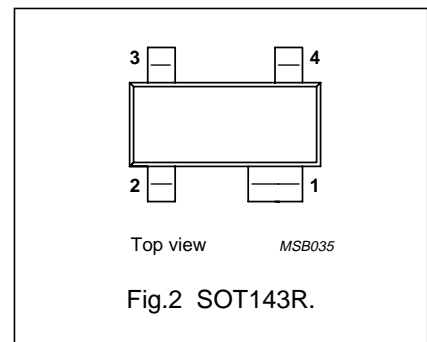
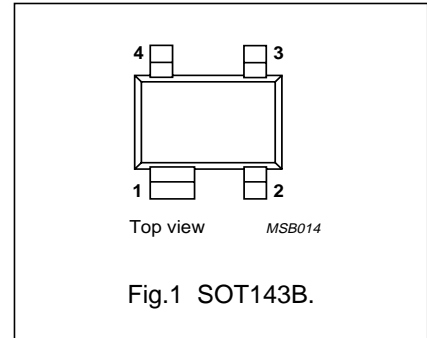
DESCRIPTION

NPN silicon planar epitaxial transistors, intended for wideband applications in the GHz range, such as analog and digital cellular telephones, cordless telephones (CT1, CT2, DECT, etc.), radar detectors, satellite TV tuners (SATV), MATV/CATV amplifiers and repeater amplifiers in fibre-optical systems.

The transistors are mounted in plastic SOT143B and SOT143R packages.

PINNING

PIN	DESCRIPTION
BFG540 (Fig.1) Code: N37	
1	collector
2	base
3	emitter
4	emitter
BFG540/X (Fig.1) Code: N43	
1	collector
2	emitter
3	base
4	emitter
BFG540/XR (Fig.2) Code: N49	
1	collector
2	emitter
3	base
4	emitter



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QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	–	15	V
I_C	DC collector current		–	–	120	mA
P_{tot}	total power dissipation	up to $T_s = 60\text{ °C}$; note 1	–	–	400	mW
h_{FE}	DC current gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_j = 25\text{ °C}$	60	120	250	
C_{re}	feedback capacitance	$I_C = 0$; $V_{CE} = 8\text{ V}$; $f = 1\text{ MHz}$	–	0.5	–	pF
f_T	transition frequency	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	18	–	dB
		$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	11	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	15	16	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 10\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.3	1.8	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.9	2.4	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 10\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	2.1	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	DC collector current		–	120	mA
P_{tot}	total power dissipation	up to $T_s = 60\text{ °C}$ (note 1)	–	400	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 60\text{ °C}$ note 1	290	K/W

Note

- T_s is the temperature at the soldering point of the collector pin.

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CHARACTERISTICS

 $T_j = 25\text{ °C}$ unless otherwise specified.

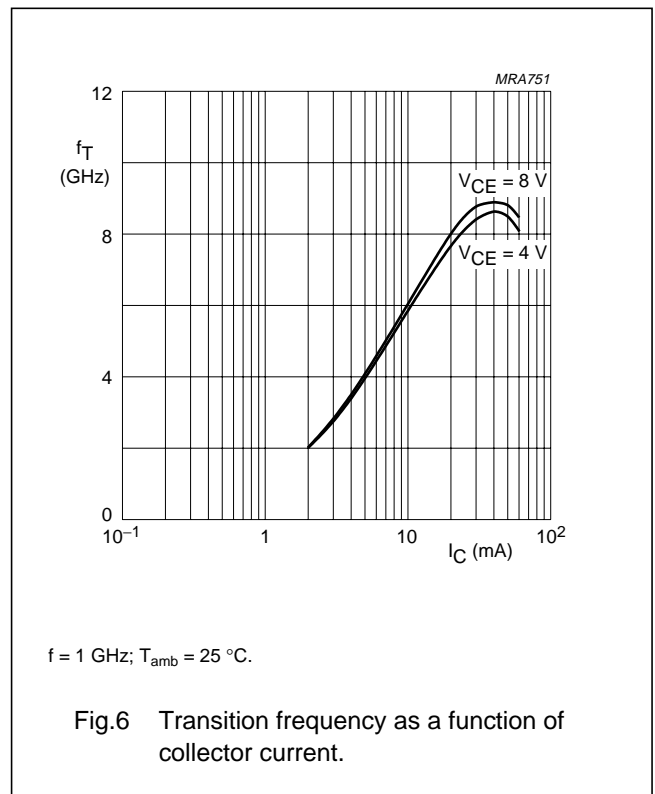
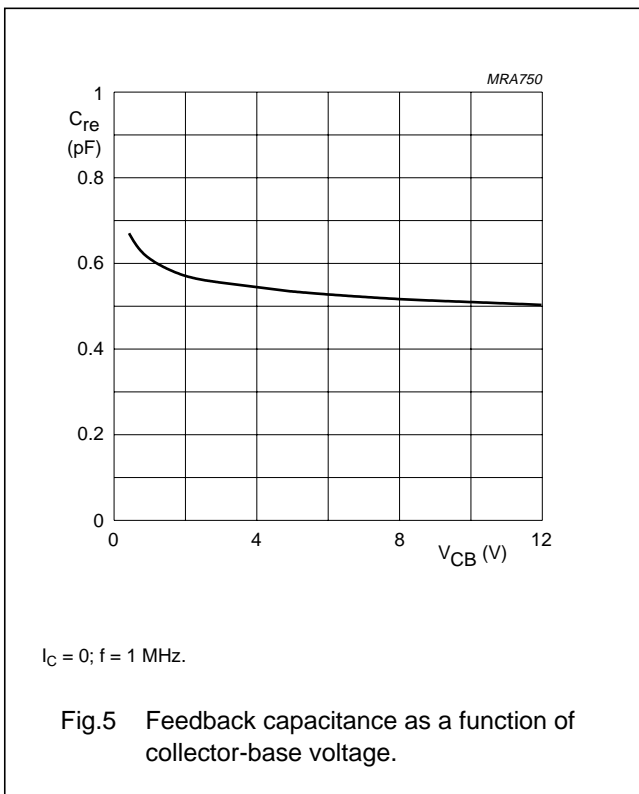
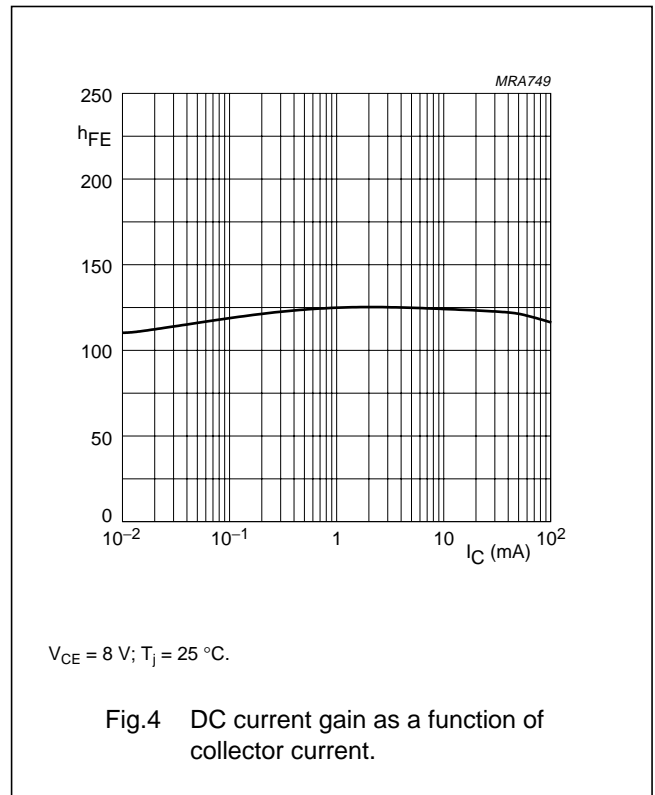
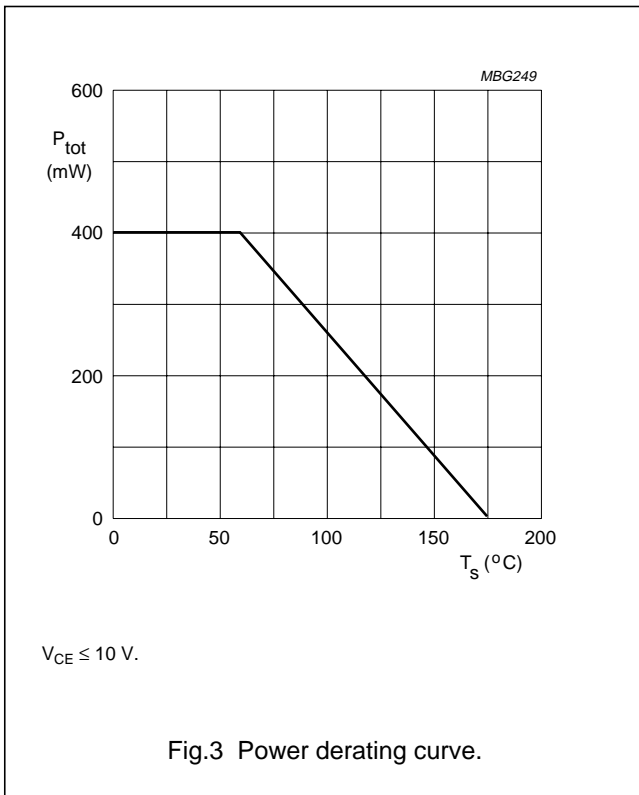
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 8\text{ V}$	–	–	50	nA
h_{FE}	DC current gain	$I_C = 40\text{ mA}; V_{CE} = 8\text{ V}$	60	120	250	
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	2	–	pF
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 8\text{ V}; f = 1\text{ MHz}$	–	0.9	–	pF
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 8\text{ V}; f = 1\text{ MHz}$	–	0.5	–	pF
f_T	transition frequency	$I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; f = 1\text{ GHz}; T_{amb} = 25\text{ °C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain (note 1)	$I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	18	–	dB
		$I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	11	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	15	16	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}; I_C = 10\text{ mA}; V_{CE} = 8\text{ V}; f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	1.3	1.8	dB
		$\Gamma_s = \Gamma_{opt}; I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	1.9	2.4	dB
		$\Gamma_s = \Gamma_{opt}; I_C = 10\text{ mA}; V_{CE} = 8\text{ V}; f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	2.1	–	dB
P_{L1}	output power at 1 dB gain compression	$I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; R_L = 50\text{ }\Omega; f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	21	–	dBm
ITO	third order intercept point	note 2	–	34	–	dBm
V_O	output voltage	note 3	–	500	–	mV
d_2	second order intermodulation distortion	note 4	–	–50	–	dB

Notes

- G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and $G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$ dB.
- $V_{CE} = 8\text{ V}; I_C = 40\text{ mA}; R_L = 50\text{ }\Omega; T_{amb} = 25\text{ °C};$
 $f_p = 900\text{ MHz}; f_q = 902\text{ MHz};$
measured at $f_{(2p-q)} = 898\text{ MHz}$ and $f_{(2q-p)} = 904\text{ MHz}.$
- $d_{im} = -60\text{ dB (DIN 45004B)}; I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; Z_L = Z_S = 75\text{ }\Omega; T_{amb} = 25\text{ °C};$
 $V_p = V_O; V_q = V_O - 6\text{ dB}; V_r = V_O - 6\text{ dB};$
 $f_p = 795.25\text{ MHz}; f_q = 803.25\text{ MHz}; f_r = 805.25\text{ MHz};$
measured at $f_{(p+q-r)} = 793.25\text{ MHz}.$
- $I_C = 40\text{ mA}; V_{CE} = 8\text{ V}; V_O = 275\text{ mV}; T_{amb} = 25\text{ °C};$
 $f_p = 250\text{ MHz}; f_q = 560\text{ MHz};$ measured at $f_{(p+q)} = 810\text{ MHz}.$

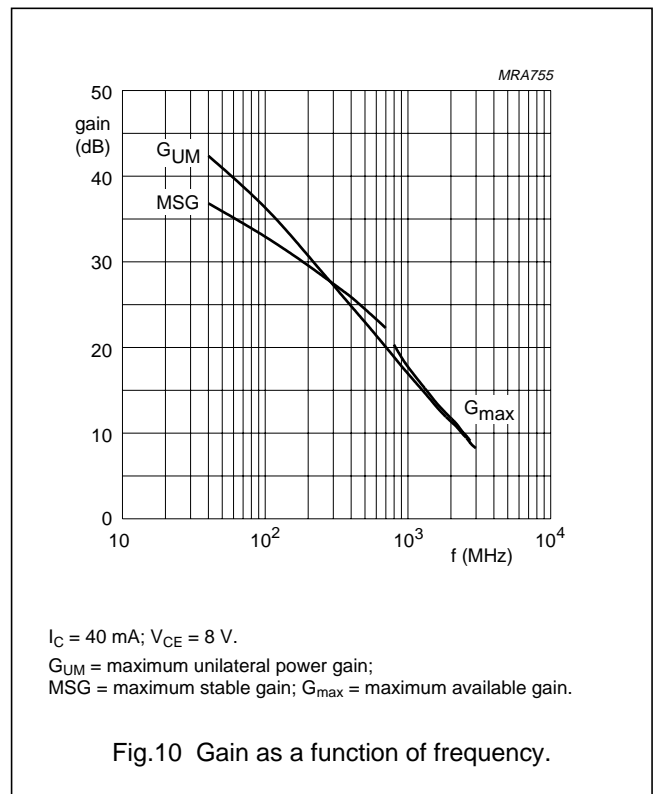
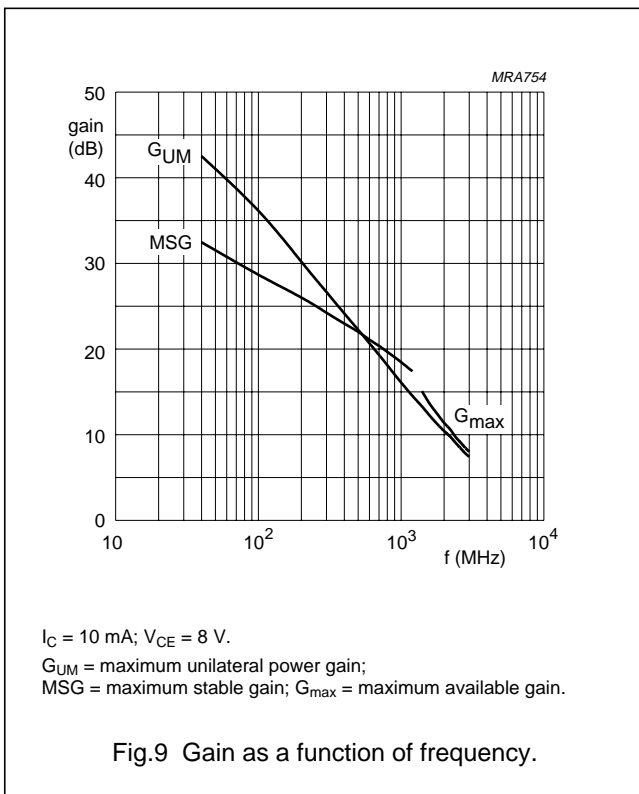
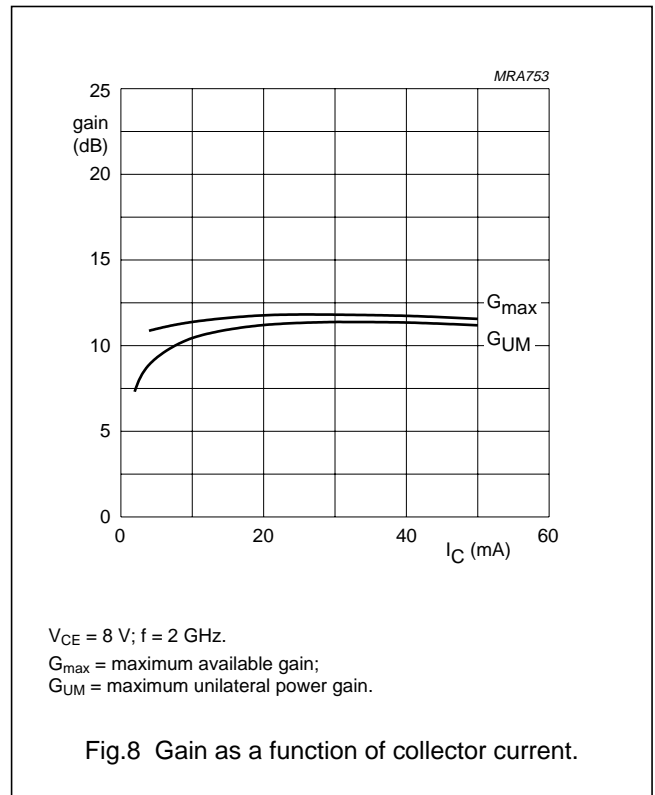
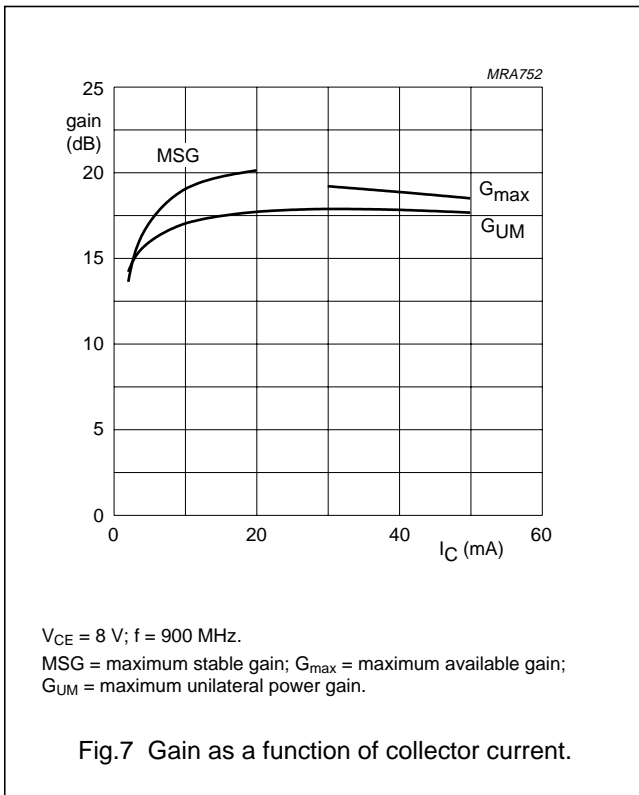
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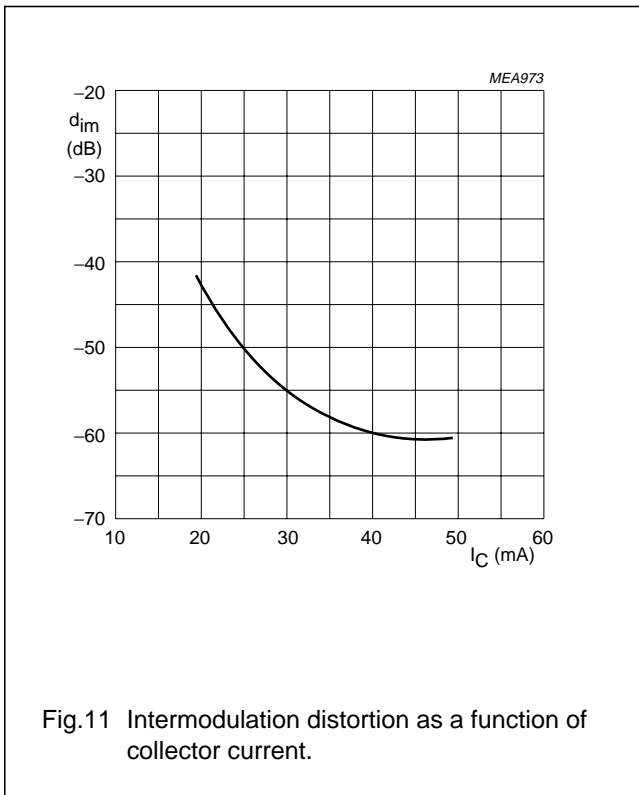


Fig.11 Intermodulation distortion as a function of collector current.

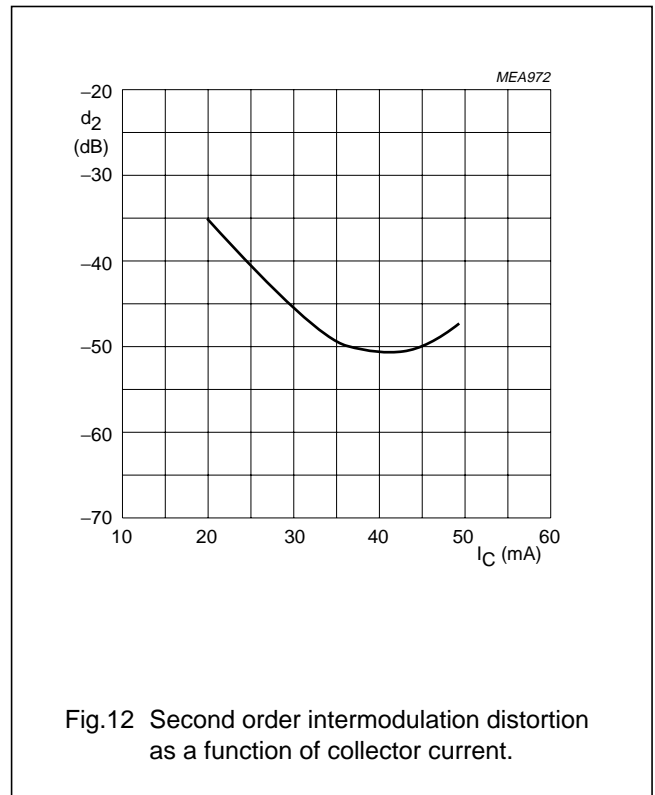
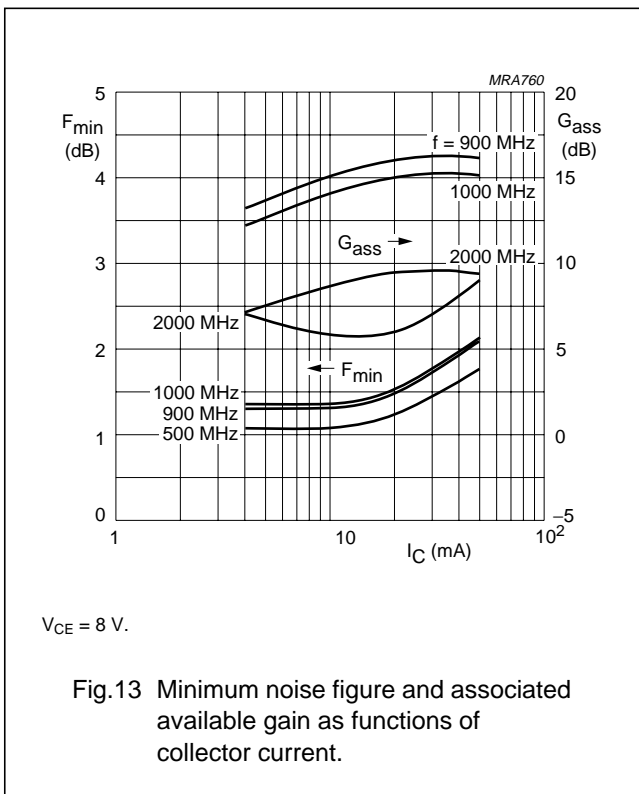
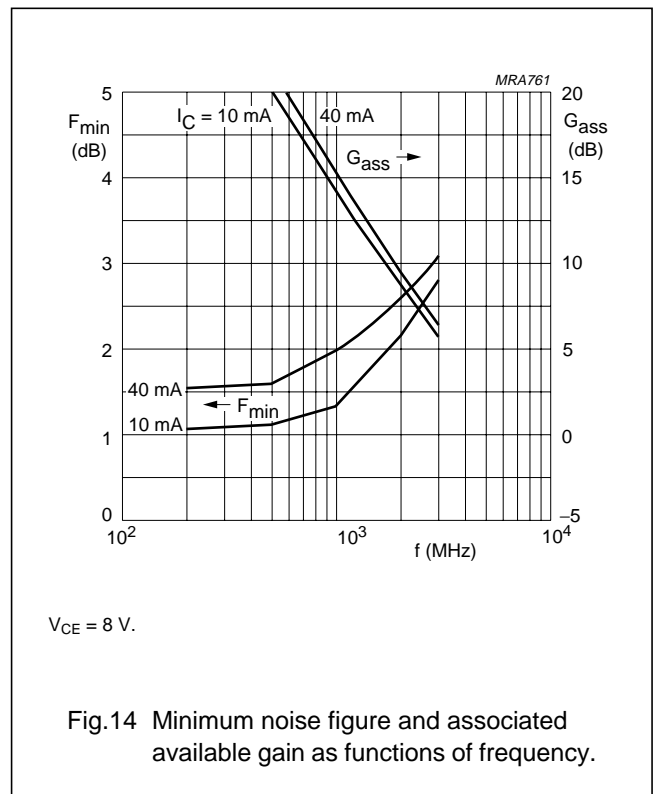


Fig.12 Second order intermodulation distortion as a function of collector current.



$V_{CE} = 8 V.$

Fig.13 Minimum noise figure and associated available gain as functions of collector current.

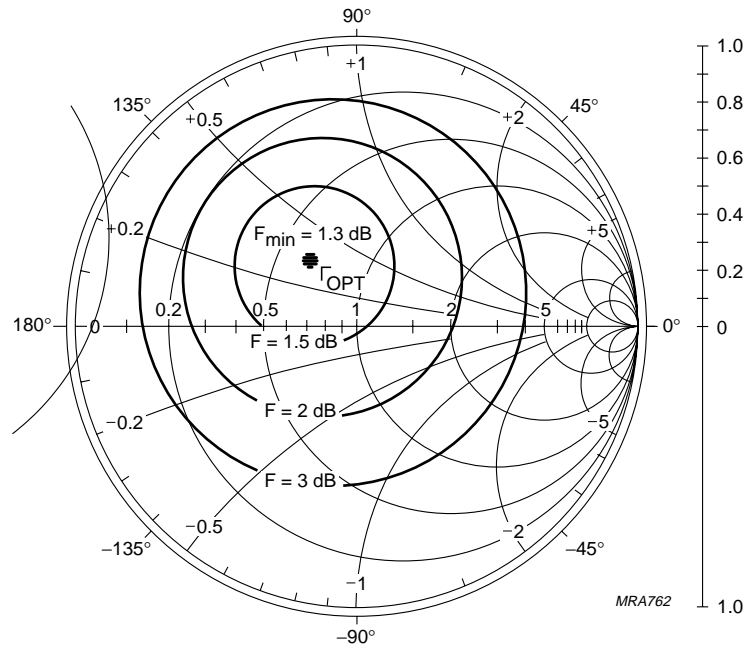


$V_{CE} = 8 V.$

Fig.14 Minimum noise figure and associated available gain as functions of frequency.

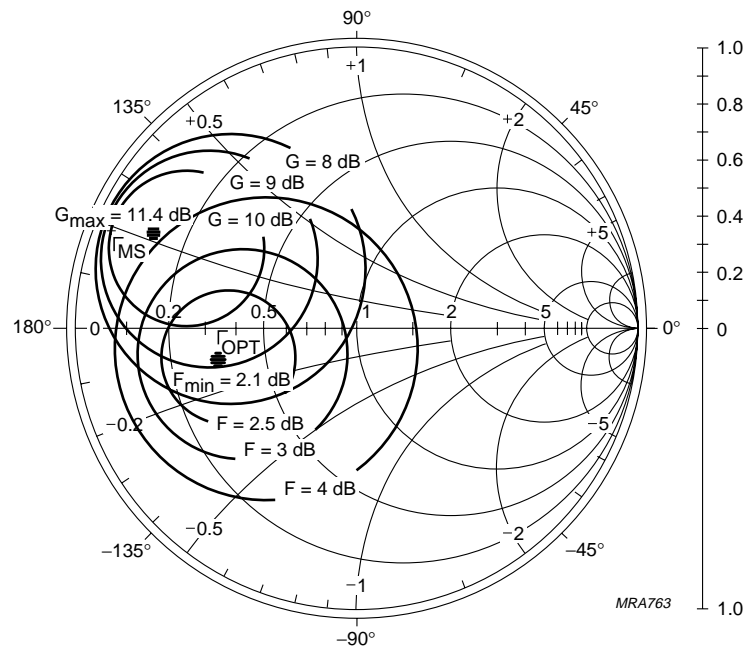
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BFG540; BFG540/X;
BFG540/XR



$I_C = 10 \text{ mA}$; $V_{CE} = 8 \text{ V}$; $Z_0 = 50 \Omega$; $f = 900 \text{ MHz}$.

Fig.15 Noise circle figure.

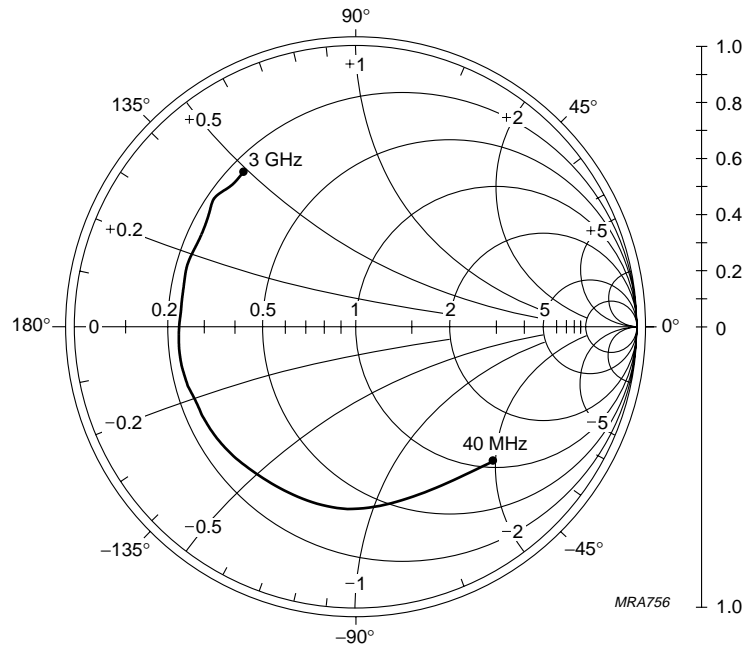


$I_C = 10 \text{ mA}$; $V_{CE} = 8 \text{ V}$; $Z_0 = 50 \Omega$; $f = 2 \text{ GHz}$.

Fig.16 Noise circle figure.

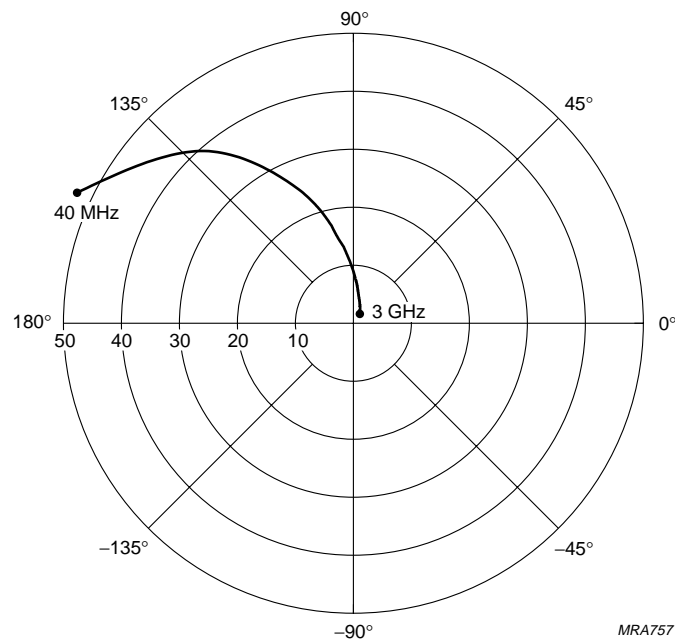
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$I_C = 40 \text{ mA}$; $V_{CE} = 8 \text{ V}$; $Z_0 = 50 \Omega$.

Fig.17 Common emitter input reflection coefficient (S_{11}).

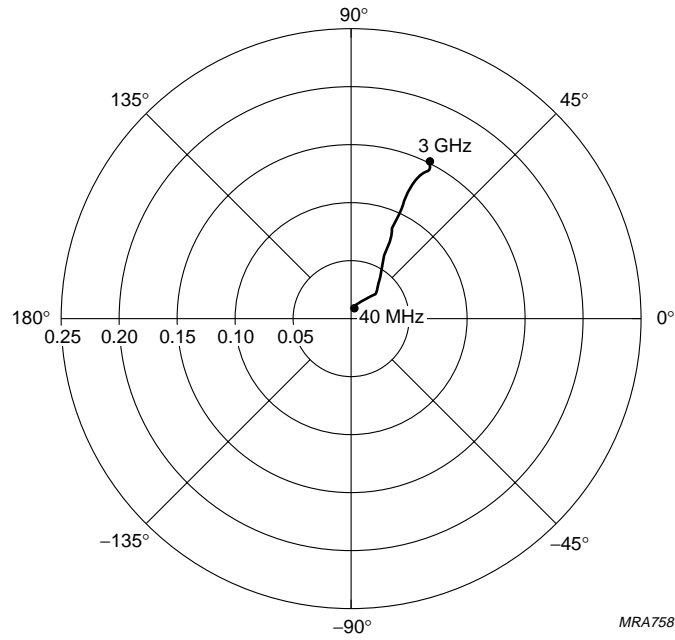


$I_C = 40 \text{ mA}$; $V_{CE} = 8 \text{ V}$.

Fig.18 Common emitter forward transmission coefficient (S_{21}).

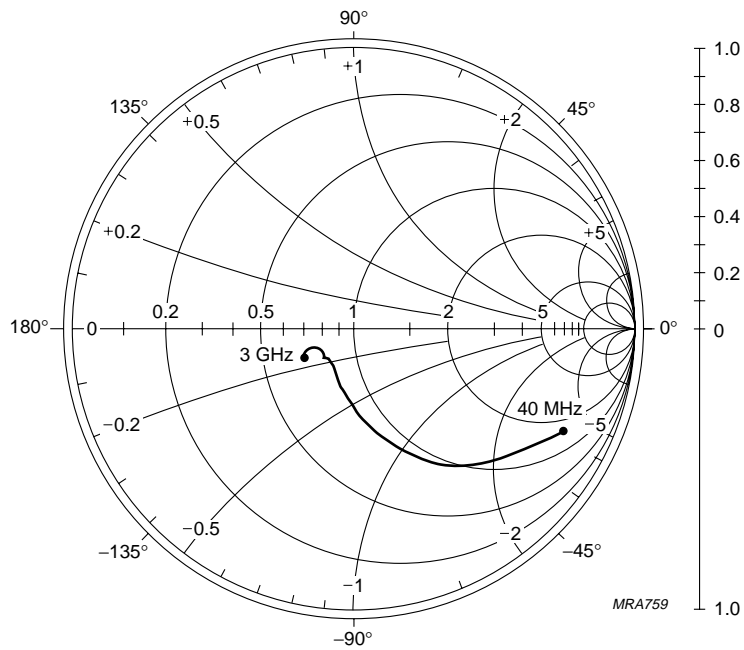
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$I_C = 40 \text{ mA}; V_{CE} = 8 \text{ V}.$

Fig.19 Common emitter reverse transmission coefficient (S_{12}).



$I_C = 40 \text{ mA}; V_{CE} = 8 \text{ V}; Z_0 = 50 \Omega.$

Fig.20 Common emitter output reflection coefficient (S_{22}).

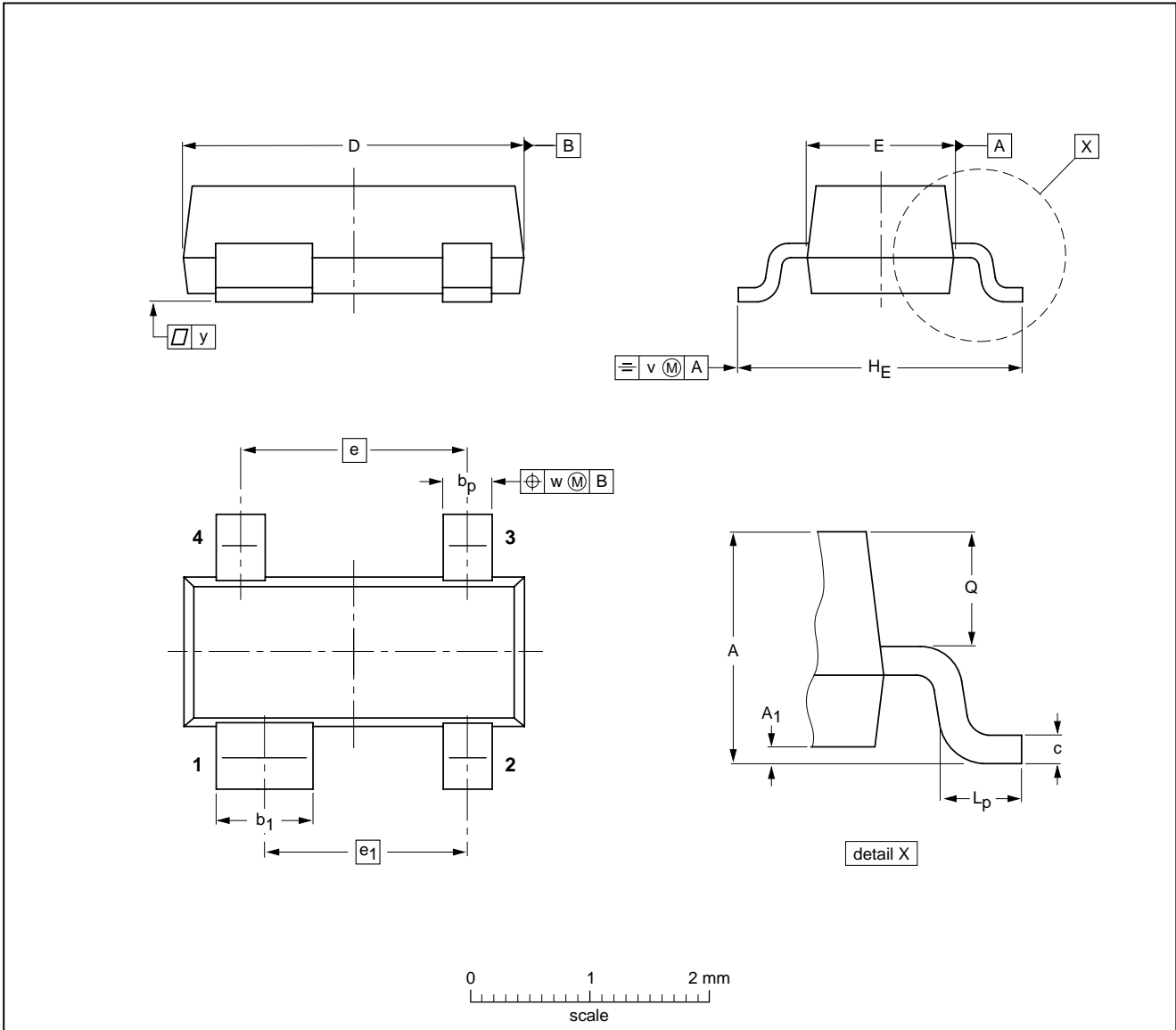
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BFG540; BFG540/X;
BFG540/XR

PACKAGE OUTLINES

Plastic surface mounted package; 4 leads

SOT143B



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

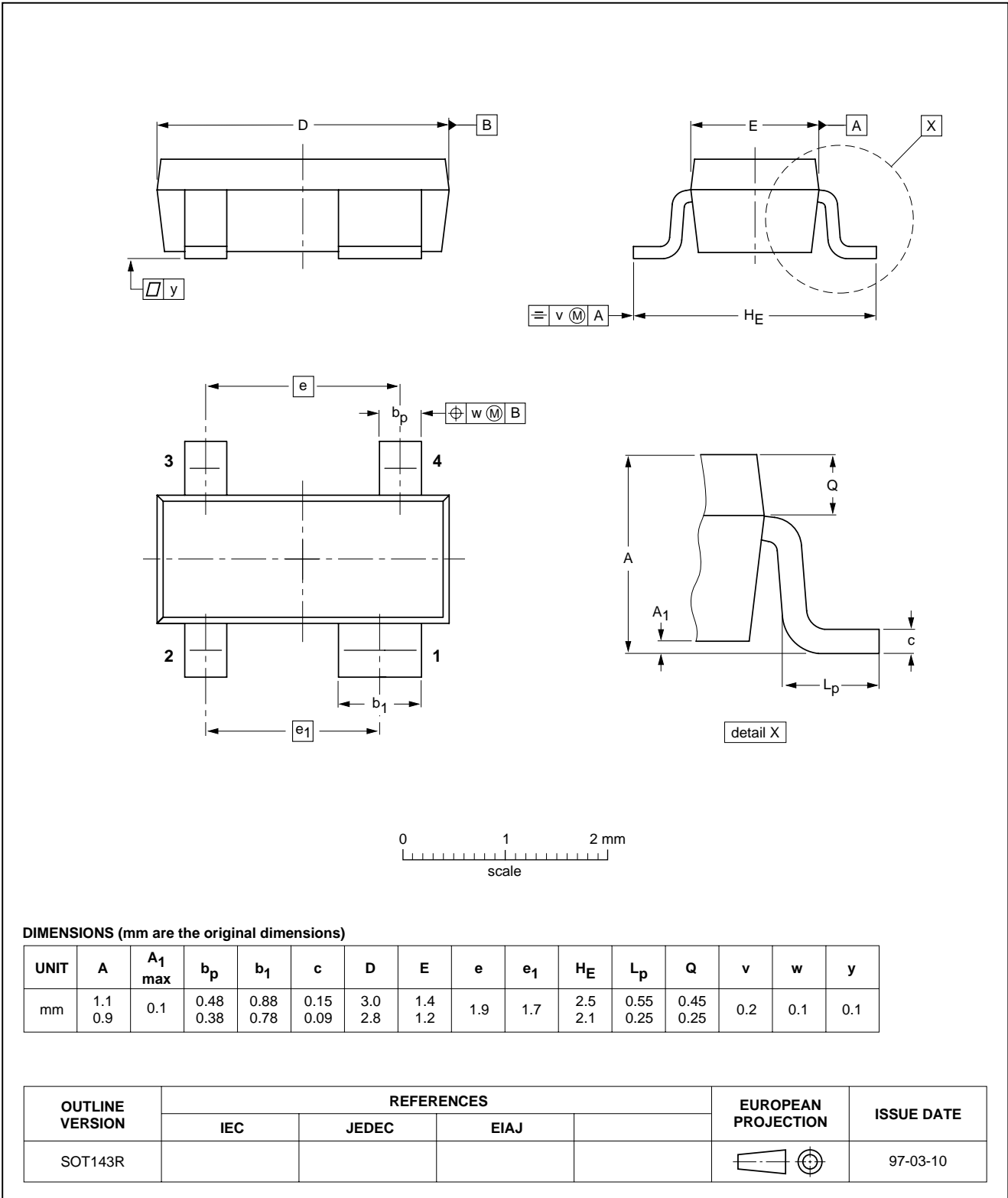
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

NPN 9 GHz wideband transistor

BFG540; BFG540/X;
BFG540/XR

Plastic surface mounted package; reverse pinning; 4 leads

SOT143R



NPN 9 GHz wideband transistor

BFG540; BFG540/X;
BFG540/XR**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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BFG540; BFG540/X;
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NOTES

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